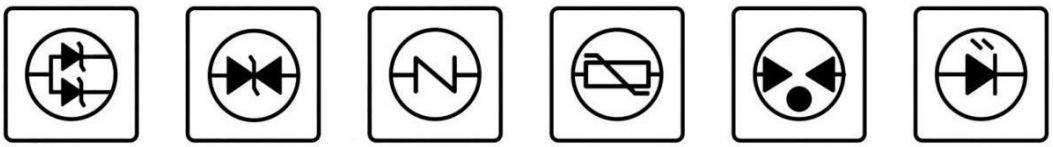
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MSZ1A05AP

Product specification

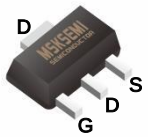
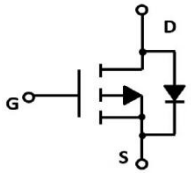
MSZ1A05AP

-100V/-5A P-Channel MOSFET

Features

- Split gate trench MOSFET technology
- Low $R_{DS(on)}$ & FOM
- Extremely low switching loss
- Excellent stability and uniformity

Reference News

SOT-89-3L	Schematic diagram	Marking
		1A05AP ****

Application

- Power management
- Portable equipment

Product Summary

V_{DS}	$R_{DS(ON)}$ MAX	I_D MAX
-100V	200mΩ@-10V	-5A
	250mΩ@-4.5V	

Absolute Maximum Ratings (TA=25℃unless otherwise noted)

Symbol	Parameter		Rating	Unit
Common Ratings (TC=25°C Unless Otherwise Noted)				
V_{DS}	Drain-Source Breakdown Voltage		-100	V
V_{GS}	Gate-Source Voltage		±20	V
T_J	Maximum Junction Temperature		150	°C
T_{STG}	Storage Temperature Range		-50 to 155	°C
I_S	Diode Continuous Forward Current	Tc=25°C	-5	A
Mounted on Large Heat Sink				
I_{DM}	Pulse Drain Current Tested	Tc=25°C	-33	A
I_D	Continuous Drain Current	Tc=25°C	-5	A
P_D	Maximum Power Dissipation	Tc=25°C	2.5	W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient		315	°C/W

Ordering Information (Example)

Type	Package	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MSZ1A05AP	SOT-89-3L	1,000	4,000	24,000	7"reel

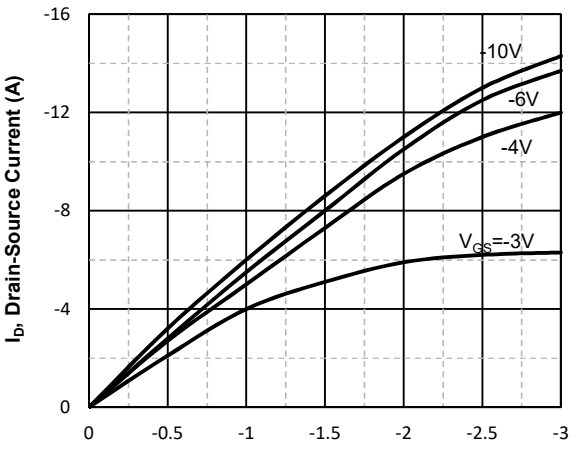
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Electrical Characteristics (TJ=25℃ unless otherwise noted)

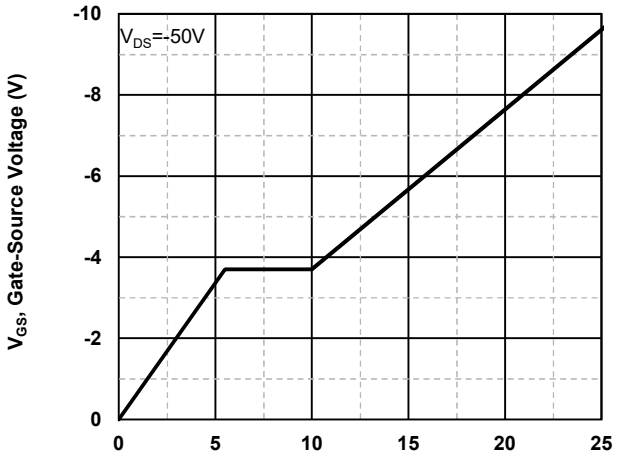
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
$BV_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=-250μA	-100	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=-100V, V_{GS}=0V	--	--	-1.0	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS}=±20V, V_{DS}=0V	--	--	±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=-250μA	-1.0	-1.8	-2.5	V
$R_{DS(on)}$	Drain-Source On-State Resistance	V_{GS}=-10V, I_D=-8A	--	155	200	mΩ
		V_{GS}=-4.5V, ID=-6A	--	170	250	mΩ
Dynamic Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
C_{ISS}	Input Capacitance	V_{DS}=-50V , V_{GS}=0V , f=1MHz	--	1488	--	pF
C_{OSS}	Output Capacitance		--	39	--	pF
C_{RSS}	Reverse Transfer Capacitance		--	30	--	pF
Switching Characteristics						
Q_g	Total Gate Charge	V_{DS}=-50V, I_D=-5A, V_{GS}=-10V	--	26.5	--	nC
Q_{gs}	Gate Source Charge		--	6	--	nC
Q_{gd}	Gate Drain Charge		--	4	--	nC
$t_{d(on)}$	Turn-on Delay Time	V_{DS}=-50, I_D=-5A, V_{GS}=-10, R_G=4.5Ω	--	14	--	nS
t_r	Turn-on Rise Time		--	45	--	nS
$t_{d(off)}$	Turn-Off Delay Time		--	227	--	nS
t_f	Turn-Off Fall Time		--	93	--	nS
Source- Drain Diode Characteristics						
V_{SD}	Forward on voltage	Tj=25℃, Is=-5A	--	-0.8	-1.2	V

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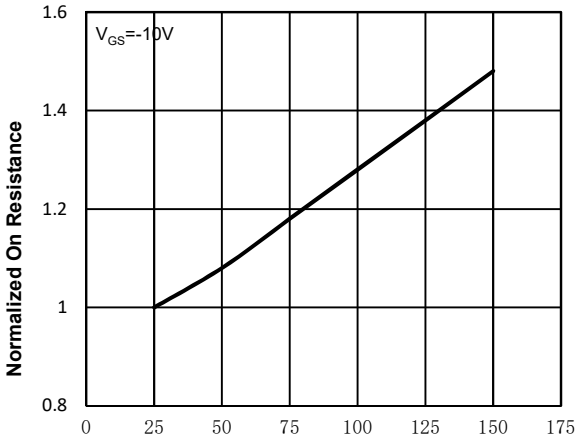
Typical Operating Characteristics



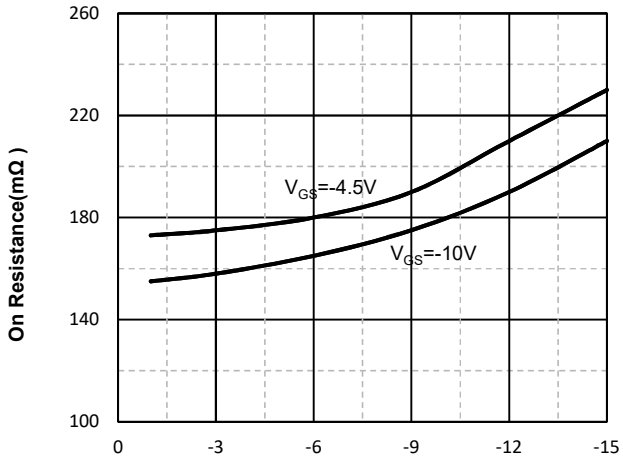
V_{DS}, Drain -Source Voltage (V)
Fig1. Typical Output Characteristics



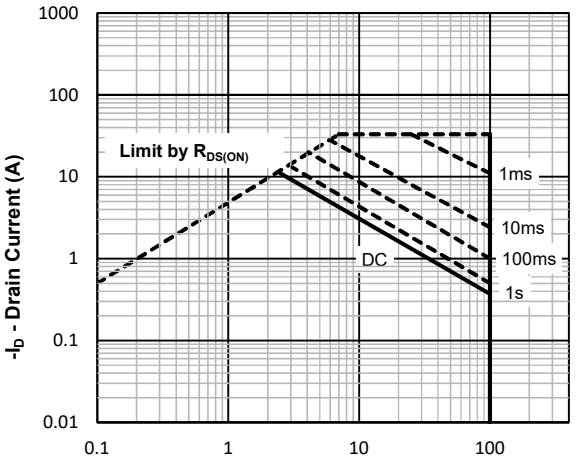
Qg -Total Gate Charge (nC)
Fig2. Typical Gate Charge Vs.Gate-Source Voltage



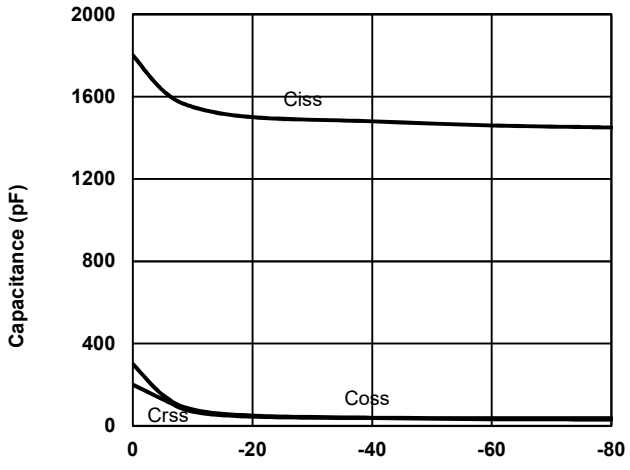
Tj - Junction Temperature (°C)
Fig3. Normalized On-Resistance Vs. Temperature



I_D, Drain-Source Current (A)
Fig4. On-Resistance Vs. Drain-Source Current



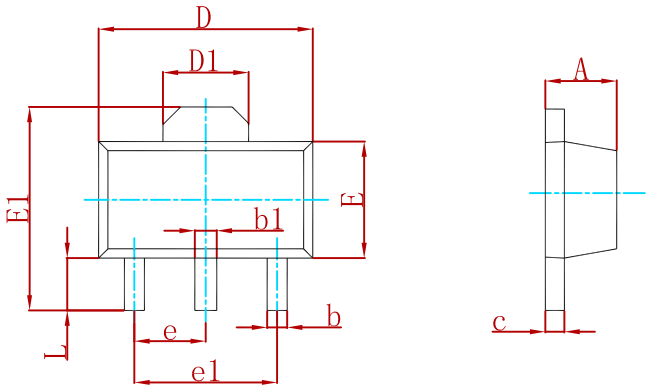
-V_{DS}, Drain -Source Voltage (V)
Fig5. Maximum Safe Operating Area



V_{DS} , Drain-Source Voltage (V)
Fig6 Typical Capacitance Vs.Drain-Source Voltage

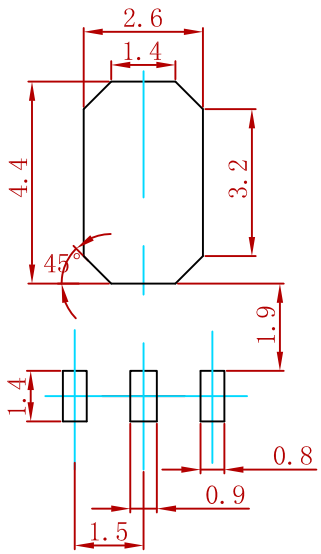
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PACKAGE MECHANICAL DATA



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.020
b1	0.400	0.580	0.016	0.023
c	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550 REF.		0.061 REF.	
E	2.300	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
e	1.500 TYP.		0.060 TYP.	
e1	3.000 TYP.		0.118 TYP.	
L	0.900	1.200	0.035	0.047

Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:±0.05mm.
3.The pad layout is for reference purposes only.

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